Shantou Huashan Electronic Devices Co.,Ltd.

PNP SILICON TRANSISTOR

HS733

APPLICATIONS

The H733 is designed for driver stage of AF amplifier
And low speed switching.

ABSOLUTE MAXIMUM RATINGS (T_a=25℃)

T_{stg}——Storage Temperature····· -55~150℃

T_j——Junction Temperature·····150℃

P_C——Collector Dissipation·····250mW

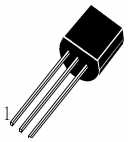
V_{CBO}——Collector-Base Voltage·····-60V

V_{CEO}——Collector-Emitter Voltage·····-50V

V_{EBO}——Emitter-Base Voltage·····-5V

I_C——Collector Current·····-150mA

TO-92



1—Emitter，E
2—Base，B
3— Collector，C

ELECTRICAL CHARACTERISTICS (T_a=25℃)

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
BV_{CBO}	Collector-Base Breakdown Voltage	-60			V	I_C=-100μA, I_E=0
BV_{CEO}	Collector-Emitter Breakdown Voltage	-50			V	I_C=-10mA, I_B=0
BV_{EBO}	Emitter-Base Breakdown Voltage	-5			V	I_E=-10μA，I_C=0
H_{FE}	DC Current Gain	70		700		V_{CE}=-6V, I_C=-1mA
$V_{CE(sat)}$	Collector- Emitter Saturation Voltage			-0.3	V	I_C=-100mA, I_B=-10mA
$V_{BE(ON)}$	Base-Emitter On Voltage	-0.5		-0.8	V	V_{CE}=-6V, I_C=-1mA
I_{CBO}	Collector Cut-off Current			-100	nA	V_{CB}=-60V, I_E=0
I_{EBO}	Emitter Cut-off Current			-100	nA	V_{EB}=-5V, I_C=0
f_T	Current Gain-Bandwidth Product	50	180		MHz	V_{CE}=-6V, I_C=-10mA
Cob	Output Capacitance		2.8		pF	V_{CB}=-6V, I_E=0，f=1MHz
NF	Noise Figure		6.0	20	dB	V_{CE}=-6V, I_C=-0.3mA, f=100Hz，Rs=10Ω

h_{FE} Classification

O	Y	GR	BL
70—140	120—240	200—400	350—700